

Excellent Integrated System Limited

Stocking Distributor

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[Diodes Incorporated](#)
[DMMT5551-7](#)

For any questions, you can email us directly:

sales@integrated-circuit.com



DMMT5551/DMMT5551S

MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

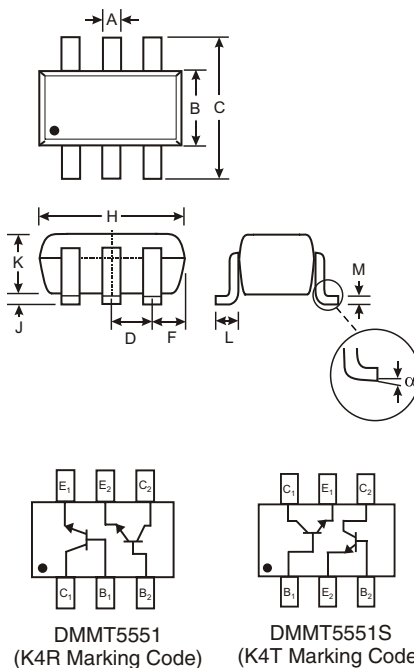
NEW PRODUCT

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DMMT5401)
- Ideal for Medium Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, h_{FE} , $V_{CE(SAT)}$, $V_{BE(SAT)}$
- 1% Matched Tolerance, Available (Note 2)
- Also Available in Lead Free Version

Mechanical Data

- Case: SOT-26, Molded Plastic
- Case Material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 8, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K4R & K4T
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approx.)



SOT-26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
F	—	—	0.55
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emmitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous (Note 3)	I_C	200	mA
Power Dissipation (Note 3, 4)	P_d	300	mW
Thermal Resistance, Junction to Ambient (Note 3)	$R_{\theta JA}$	417	K/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. Built with adjacent die from a single wafer.
 2. Contact the Diodes, Inc. Sales department.
 3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 4. Maximum combined dissipation.

Electrical Characteristics @ T_A = 25°C unless otherwise specified

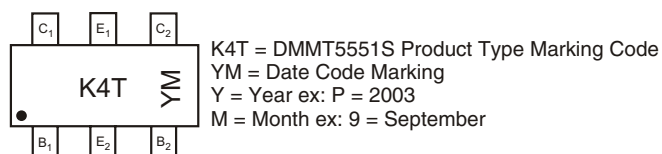
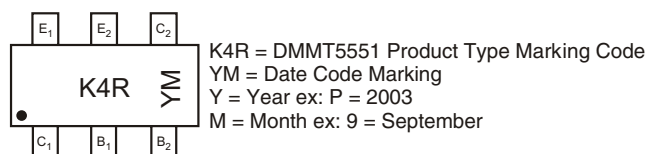
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	50	nA μA	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	—	50	nA	V _{EB} = 4.0V, I _C = 0
ON CHARACTERISTICS (Note 5)					
DC Current Gain (Note 6)	h _{FE}	80 80 30	— 250 —	—	I _C = 1.0mA, V _{CE} = 5.0V I _C = 10mA, V _{CE} = 5.0V I _C = 50mA, V _{CE} = 5.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.15 0.20	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	1.0	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	6.0	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Small Signal Current Gain	h _{FE}	50	250	—	V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V _{CE} = 5.0V, I _C = 200μA, R _S = 1.0kΩ, f = 1.0kHz

Ordering Information (Note 7)

Device	Packaging	Shipping
DMMT5551-7	SOT-26	3000/Tape & Reel
DMMT5551S-7	SOT-26	3000/Tape & Reel

- Notes:
5. Short duration test pulse used to minimize self-heating effect.
 6. The DC Current Gain, h_{FE}, (matched at I_C = 10mA and V_{CE} = 5V) Collector Emitter Saturation Voltage, V_{CE(SAT)}, and Base Emitter Saturation Voltage, V_{BE(SAT)} are matched with typical matched tolerances of 1% and maximum of 2%.
 7. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 8. For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above.
Example: DMMT5551-7-F.

Marking Information

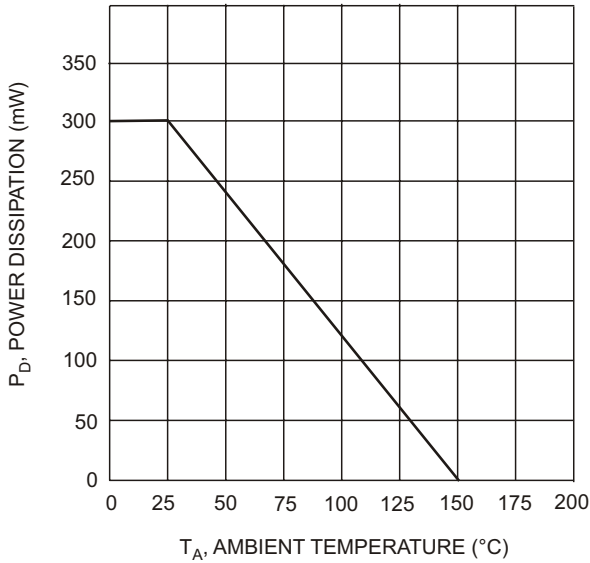


Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

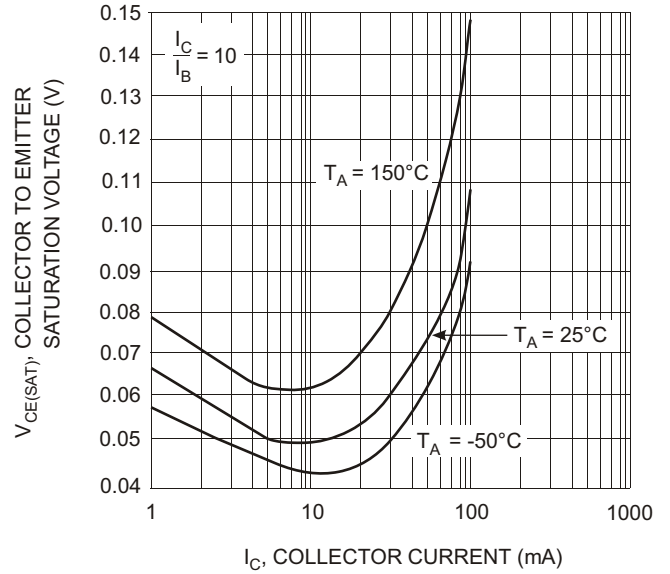
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

NEW PRODUCT



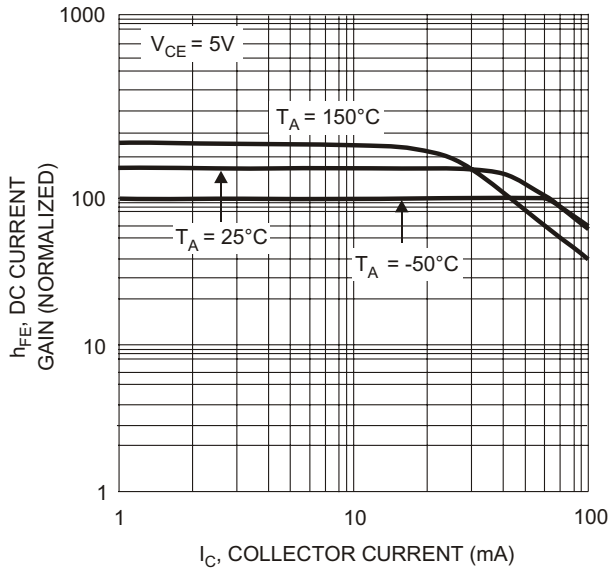
T_A , AMBIENT TEMPERATURE (°C)

Fig. 1, Max Power Dissipation vs Ambient Temperature



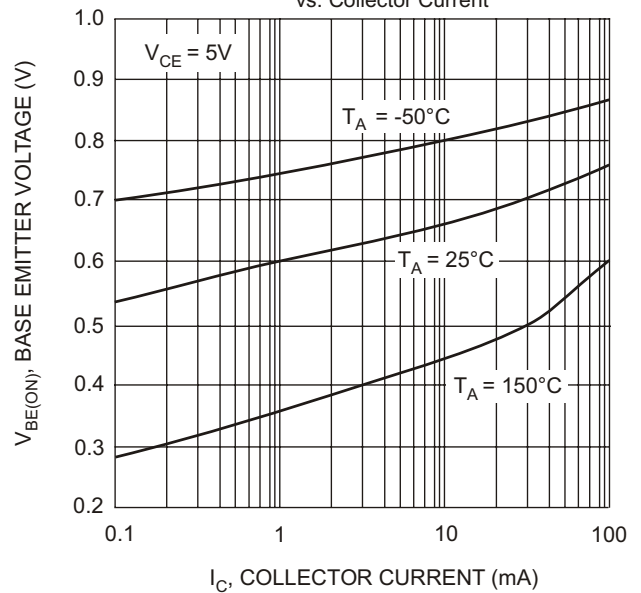
I_C , COLLECTOR CURRENT (mA)

Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



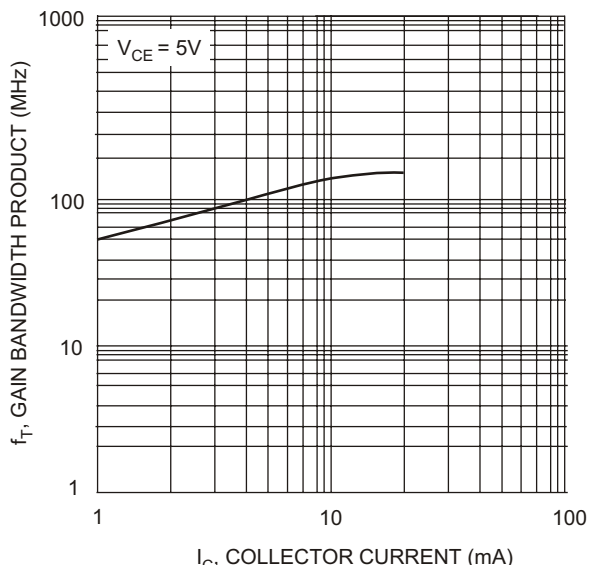
I_C , COLLECTOR CURRENT (mA)

Fig. 3, DC Current Gain vs Collector Current



I_C , COLLECTOR CURRENT (mA)

Fig. 4, Base Emitter Voltage vs. Collector Current



I_C , COLLECTOR CURRENT (mA)

Fig. 5, Gain Bandwidth Product vs. Collector Current